RENESAS

RL78/I1A

RENESAS MCU

Datasheet

R01DS0171EJ0320 Rev.3.20 Sep 29, 2017

True Low Power Platform, High Resolution PWM and Rich Analog, 2.7 V to 5.5 V operation, 32 to 64 Kbyte Flash, for Inverter Control, Digital Power Control and Lighting Control Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.7 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.60 μA
- Operating: 156.25 µA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC architecture (Harvard) with 3-stage pipeline
- Multiply signed & unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- Density: 32 KB to 64 KB
- Block size: 1 KB

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- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data flash with background operation
- Data flash size: 4 KB
- Erase cycles: 1 million (typ.)
- Erase/programming voltage: 2.7 V to 5.5 V

RAM

- 2 KB to 4 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 32 MHz with +/- 1% accuracy over voltage (2.7 V to 5.5 V) and temperature (-20°C to 85°C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 6 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

16-bit timers KB0 to KB2, and KC0 for PWM output

16-bit timers KB0 to KB2: maximum 6 outputs (3 channels × 2)

- Smooth start function, dithering function, forced output stop function (unsynchronized with comparator or external interrupt) enables over-voltage protection, over-current protection and peak current control, and single/interleave PFC function
- Average resolution < 0.98 nsec output, 64 MHz (when using PLL) + dithering option
- 16-bit timer KC0 (1 channel × 6 (output))
- PWM output gating function by interlocking with 16-bit timers KB0, KB1, and KB2

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Multiple Communication Interfaces

- Up to 1 channel x I²C multi-master (SMBus/PMBus support)
- Up to 1 channel x CSI/SPI (7-, 8-bit)
- Up to 3 channels x UART (7-, 8-, 9-bit), DALI support 1 channel (8-, 16-, 17-, 24-bit, master and slave)
- Up to 1 channel x LIN

Rich Analog

- \bullet ADC: Up to 11 channels, 8/10-bit resolution, 2.125 μs conversion time
- Supports 2.7 V
- Internal voltage reference (1.45 V)
- Comparator: High response time 70 ns (typ.), up to 6 channels, internal DAC 3 channels 8-bit resolution, window comparator mode
- PGA (x4 to x32): 6 input channels
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM/SFR write protection
- Illegal memory access detection
- Clock stop/frequency detection
- ADC self-test
- General Purpose I/O
- 5-V tolerant, high-current (up to 8.5 mA per pin)
 Open-drain, internal pull-up support

Operating Ambient Temperature

- Standard: –40°C to +105°C
- Extend: -40°C to +125°C

Package Type and Pin Count SSOP: 20, 30, 38



• ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/I1A				
			20 pins	30 pins	38 pins		
64 KB	4 KB	4 KB ^{Note}	_	R5F107AE	R5F107DE		
32 KB	4 KB	2 KB	R5F1076C	R5F107AC	-		

Note This is about 3 KB when the self-programming function and data flash function are used.



1.2 List of Part Numbers

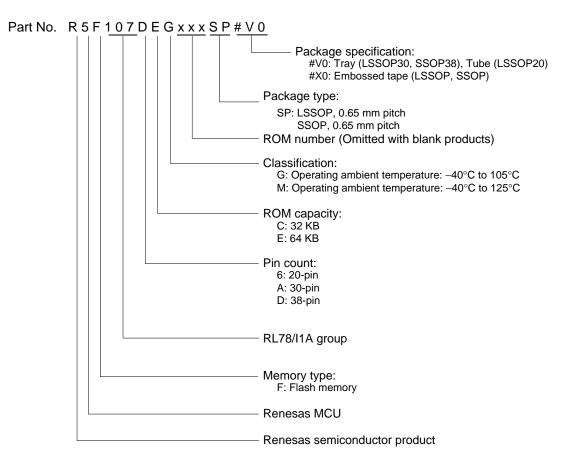


Figure 1-1. Part Number, Memory Size, and Package of RL78/I1A

Pin count	Package	Operating Ambient Temperature	Part Number
20 pins	20-pin plastic LSSOP	TA = -40 to +105°C	R5F1076CGSP#V0, R5F1076CGSP#X0
	(4.4 × 6.5)	TA = -40 to +125°C	R5F1076CMSP#V0, R5F1076CMSP#X0
30 pins 30-pin plastic LSSOP (7.62 mm (300))		TA = -40 to +105°C	R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0
		TA = -40 to +125°C	R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0
38 pins	38-pin plastic SSOP	T _A = -40 to +105°C	R5F107DEGSP#V0, R5F107DEGSP#X0
	(7.62 mm (300))	TA = -40 to +125°C	R5F107DEMSP#V0, R5F107DEMSP#X0

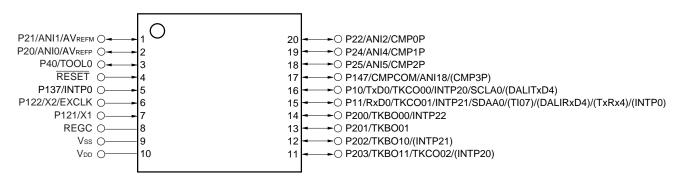
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

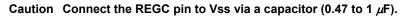


1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (4.4 x 6.5)





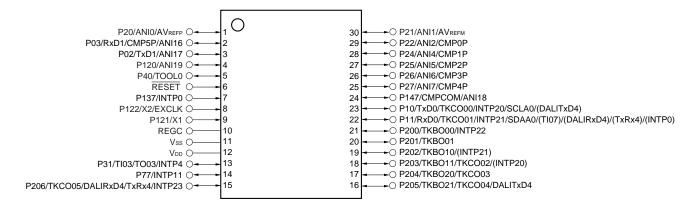
Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
- **3.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).



1.3.2 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300))



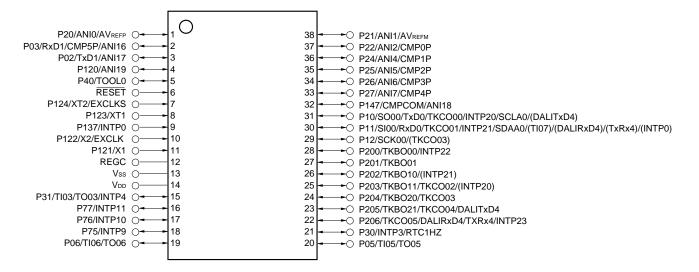
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.3.3 38-pin products

• 38-pin plastic SSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



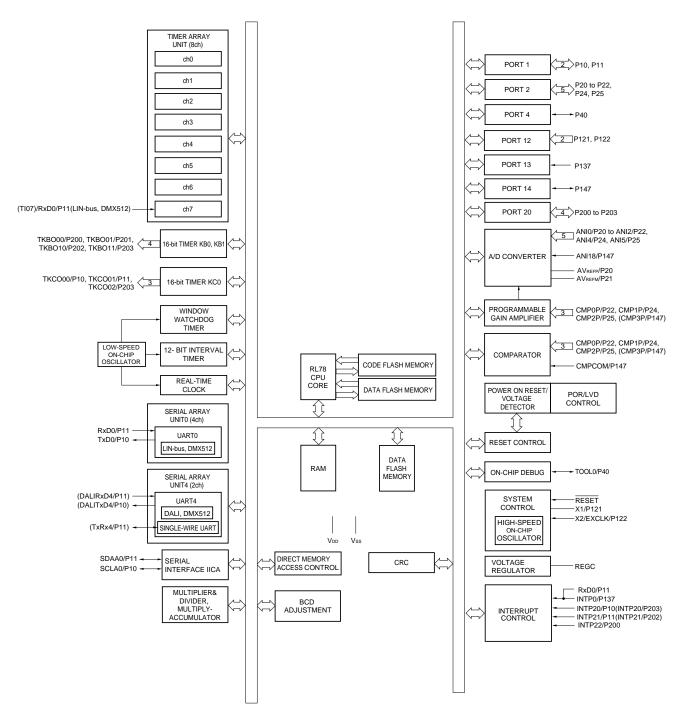
1.4 Pin Identification

ANI0 to ANI2,		REGC:	Regulator Capacitance
ANI4 to ANI7,		RESET:	Reset
ANI16 to ANI19:	Analog Input	RTC1HZ:	Real-time Clock Correction Clock
AVREFM:	Analog Reference Voltage Minus		(1 Hz) Output
AVREFP:	Analog Reference Voltage Plus	RxD0, RxD1,	
CMP0P to CMP5P:	Comparator Analog Input	DALIRxD4:	Receive Data
CMPCOM:	Comparator External Reference	SCK00:	Serial Clock Input/Output
	Voltage	SCLA0:	Serial Clock Input/Output
EXCLK:	External Clock Input (Main System	SDAA0:	Serial Data Input/Output
	Clock)	SI00:	Serial Data Input
EXCLKS:	External Clock Input (Subsystem	SO00:	Serial Data Output
	Clock)	TI03, TI05, TI06,	
INTP0, INTP3,		TI07:	Timer Input
INTP4, INTP9,		TO03, TO05, TO06,	
INTP10, INTP11,		TKBO00, TKBO01 to	0
INTP20 to INTP23:	Interrupt Request from Peripheral	TKBO20, TKBO21,	
P02, P03,		TKCO00 to TKCO05	: Timer Output
P05, P06:	Port 0	TOOL0:	Data Input/Output for Tool
P10 to P12:	Port 1	TxRx4:	Serial Data Input/Output for Single
P20 to P22,			Wired UART
P24 to P27:	Port 2	TxD0, TxD1	
P30, P31:	Port 3	DALITxD4:	Transmit Data
P40:	Port 4	Vdd:	Power Supply
P75 to P77:	Port 7	Vss:	Ground
P120 to P124:	Port 12	X1, X2:	Crystal Oscillator (Main System Clock)
P137:	Port 13	XT1, XT2:	Crystal Oscillator (Subsystem Clock)
P147:	Port 14		
P200 to P206:	Port 20		



1.5 Block Diagram

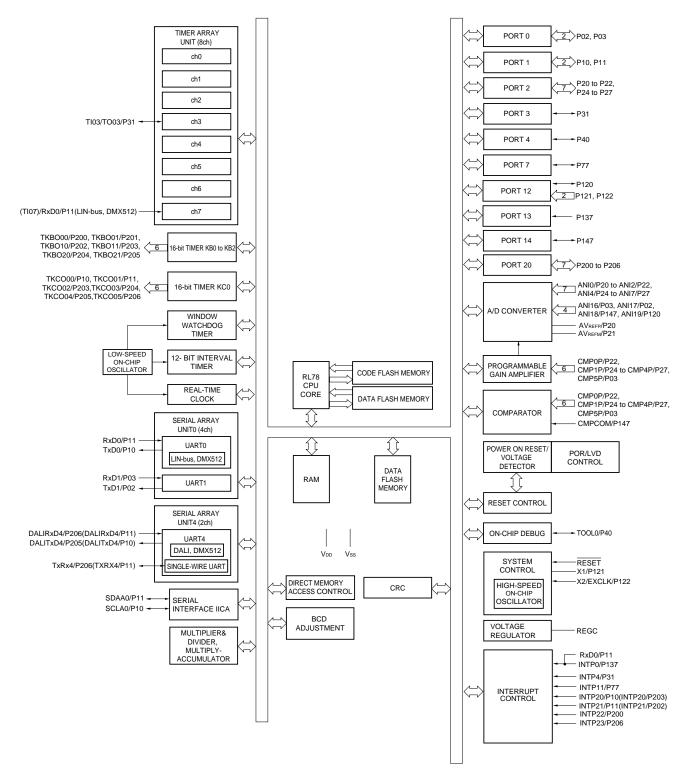
1.5.1 20-pin products



- Remarks 1. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
 - **2.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).



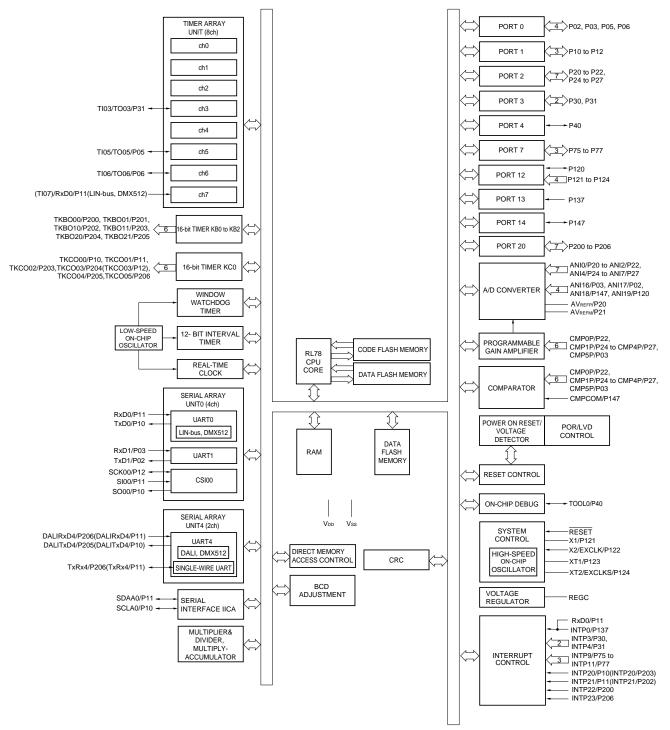
1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.5.3 38-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR1) is set to 00H.

					(1/3)			
	Item	20-pin	30	-pin	38-pin			
		R5F1076C	R5F107AC	R5F107AE	R5F107DE			
Code flash m	emory (KB)	32	32	64	64			
Data flash me	emory (KB)	4	4	4	4			
RAM (KB)		2	2	4 ^{Note 1} 4 ^{Note 1}				
Address spac	e	1 MB						
Main system clock	High-speed system clock	HS (High-speed main)	cillation, external main symbols mode: 1 to 20 MHz (Vpp node: 1 to 8 MHz (Vpp =	,				
High-speed on-chip oscillatorHS (High-speed main) mode:1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), 1 to 8 MHz (V_{DD} = 2.7 to 5.5 V)								
Clock for 16-b and KC0	bit timers KB0 to KB2,	64 MHz (TYP.)						
Subsystem cl only)	ock (38-pin products	XT1 (crystal) oscillation 32.768 kHz	, external subsystem clo	ck input (EXCLKS)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)						
General-purp	ose register	(8-bit register \times 8) \times 4 banks						
Minimum inst	ruction execution time	0.03125 µs (High-speed on-chip oscillator: fiн = 32 MHz operation)						
		0.05 μ s (High-speed system clock: f _{MX} = 20 MHz operation)						
		30.5 µs (Subsystem clo	ck: fsuв = 32.768 kHz ор	eration) (38-pin products o	nly)			
Instruction se	t	 8-bit operation, 16-bit Multiplication (8 bits > Bit manipulation (Set, 		n operation), etc.				
I/O port	Total	16		26	34			
	CMOS I/O	13		23	29			
	CMOS input	3		3	5			
	CMOS output	-		-	-			
Timer	16-bit timer TAU	8 channels (no timer output)	8 channels (timer outpu	t: 1, PWM output: 1 ^{Note 2})	8 channels (timer outputs: 3, PWM outputs: 3 ^{Note 2})			
	16-bit timer KB	2 channels (PWM outputs: 4)	3	channels (PWM outputs: 6)			
	16-bit timer KC	1 channel (PWM outputs: 3)	1 channel (PWM outputs: 6)					

Notes 1. This is about 3 KB when the self-programming function and data flash function are used. (For details, see CHAPTER 3 in the RL78/I1A User's Manual.)

The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/I1A User's Manual).



					(2/3)		
	Item		20-pin	30-pin	38-pin		
			R5F1076C	R5F107AC, R5F107AE	R5F107DE		
Timer	Natchdog	g timer		1 channel			
	Real-time RTC)	clock		1 channel ^{Notes 1, 2}			
	12-bit inte IT)	erval timer		1 channel			
	RTC outp	out		-	1 1 Hz (subsystem clock f _{SUB} = 32.768 kHz)		
8/10-bit resoluti	on A/D co	onverter	6 channels	11 channels	11 channels		
Comparator			4 channels	6 channels	6 channels		
Programmable	gain amp	lifier		1 channel	·		
		Input ^{Note 3}	4 channels	6 channels	6 channels		
Serial interface			[20-pin] Note 5		·		
			UART (Supporting LIN-bus and DMX512): 1 channel				
			UART (Supporting DALI	communication): 1 channel			
			[30-pin products]				
			UART (Supporting LIN-bus and DMX512): 1 channel				
			UART: 1 channel				
			UART (Supporting DALI	communication): 1 channel			
			[38-pin products]				
			CSI: 1 channel/UART (SUART: 1 channel	Supporting LIN-bus and DMX512): 1 chan	nel		
			UART (Supporting DALI	communication): 1 channel			
	l ² C b	us	1 channel	1 channel	1 channel		
Multiplier and d accumulator	vider/mul	ltiply-	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 				
DMA controller				2 channels			
Vectored interru	pt Interr	nal	27	30	30		
sources	Exter		7	10	11		
Reset			 Reset by RESET pin Internal reset by watchd Internal reset by power-orego internal reset by voltage Internal reset by illegal in Internal reset by RAM page 	on-reset detector nstruction execution ^{Note 4}			
			 Internal reset by illegal-r 	-			

Notes 1. The subsystem clock (fsub) can be selected as the operating clock only for 38-pin products.

2. The 20- and 30-pin products can only be used as the constant-period interrupt function.

- 3. The comparator input is alternatively used with analog input pin (ANI pin).
- The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or onchip debug emulator.
- 5. The 20 pin products can only be used 1 UART simultaneously due to sharing of the same I/O pins.



			(3/3)			
Item	20-pin	30-pin	38-pin			
	R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)				
Voltage detector	0 0	V to 4.06 V (6 stages) 5 V to 3.98 V (6 stages)				
On-chip debug function	Provided					
Power supply voltage	V _{DD} = 2.7 to 5.5 V					
Operating ambient temperature	T _A = -40 to +105°C (G:	$T_A = -40$ to +105°C (G: Industrial applications), $T_A = -40$ to +125°C (M: Industrial applications)				



2. ELECTRICAL SPECIFICATIONS (G: Industrial applications, $T_A = -40$ to +105°C)

In this chapter, shows the electrical specifications of the target products. Target products (G: Industrial applications): $T_A = -40$ to $+105^{\circ}C$ R5F107xxGxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.



2.1 Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		–0.5 to +6.5	V
REGC pin input voltage	Viregc	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3 $^{\text{Note 1}}$	V
Input voltage	Vi1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Vaii	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

Absolute Maximum Ratings (T_A = 25°C) (1/2)

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - 2. AV_{REF (+)}: + side reference voltage of the A/D converter.
 - **3.** Vss: Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		–170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lol1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	IOL2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory p	In flash memory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (T_A = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/crystal resonator		1.0		20.0	MHz
XT1 clock oscillation frequency $(f_{XT})^{Note}$	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.



2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator		T _A = -20 to 85°C	-1		+1	%
clock frequency accuracy ^{Note 2}		T _A = -40 to 105°C	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

2.2.3 PLL characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f_{MX} = 4 MHz)	3.94	4.00	4.06	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (fiн = 4 MHz)	3.94	4.00	4.06	MHz
PLL output clock frequency ^{Note}	fpll			$f_{\text{PLLIN}} imes 16$		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-12.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-4.0	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-30.0	mA
			$2.7~V \leq V_{\text{DD}} < 4.0~V$			-10.0	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-30.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-14.0	mA
Іон2	Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.7	mA

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor \leq 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated

with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (Iон × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	IOL1	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			7.5	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
			$2.7~V \leq V_{\text{DD}} < 4.0~V$			17.5	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			80.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			25.0	mA
	IOL2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			2.8	mA

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	2.1		Vdd	V
			TTL input buffer $3.3~V \leq V_{\text{DD}} < 4.0~V$	2.0		Vdd	V
			TTL input buffer $2.7 \ V \leq V_{\text{DD}} < 3.3 \ V$	1.5		Vdd	V
Input voltage, low	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	VIL2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \leq V_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $2.7 \ V \leq V_{\text{DD}} < 3.3 \ V$	0		0.32	V

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ mA \end{array} \end{array} \label{eq:eq:entropy}$	$V_{\text{DD}}-0.7$			V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh1 = -1.0 mA	$V_{\text{DD}}-0.5$			V
	Vон2	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh2 = -100 μ A	$V_{\text{DD}}-0.5$			V
Output voltage, low			$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:DD}$			0.7	V
		P200 to P206	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 4.0 \ mA \end{array} \end{array} \label{eq:DD}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ lol1 = 1.5 mA			0.4	V
	Vol.2 P20 to P22, P24 to P27		$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol2 = 400 μ A			0.4	V

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Condition	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = VDD				1	μA
	Ilih2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	ILIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = Vss				-1	μA
	Ilil2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	Vı = Vss, In	input port	10	20	100	kΩ

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)



2.3.2 Supply current characteristics

1	T _A = -40 to	+105°C	27V	< Vnn <	55V	$V_{SS} = 0$	N N	(1/2)
	1 = -40 10	T105 C,	Z./ V		≤ 0.0 v,	v 55 - C	' ¥)	(1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	f⊮ = 32 MHz ^{Note 3}	V _{DD} = 5.0 V		5.0	7.5	mA
Current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		5.0	7.5	mA
			mode	f⊩ = 24 MHz ^{Note 3}	V _{DD} = 5.0 V		3.9	5.8	mA
					V _{DD} = 3.0 V		3.9	5.8	mA
				f⊩ = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.2	mA
					V _{DD} = 3.0 V		2.9	4.2	mA
			LS (low- speed main) mode ^{Note 5}	$f_{H} = 8 \text{ MHz}^{\text{Note 3}},$ TA = -40 to + 85°C	V _{DD} = 3.0 V		1.3	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.0	mA
			modense	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.0	mA
			f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA	
				V _{DD} = 5.0 V	Resonator connection		2.0	2.9	mA
			f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA	
			V _{DD} = 3.0 V	Resonator connection		2.0	2.9	mA	
		LS (low-	f _{MX} = 8 MHz ^{Note 2} ,	Square wave input		1.2	1.8	mA	
			speed main) mode ^{Note 5}	V _{DD} = 3.0 V, TA = -40 to + 85°C	Resonator connection		1.2	1.8	mA
			HS (high-	fi⊢ = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		5.4	8.5	mA
			speed main) mode ^{Note 5}	fpll = 64 MHz, fclk = 32 MHz	V _{DD} = 3.0 V		5.4	8.5	mA
			mode	fi⊢ = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	5.7	mA
				fpll = 64 MHz, fclк = 16 MHz	V _{DD} = 3.0 V		3.3	5.7	mA
			Subsystem	fsue = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		4.4	6.2	μA
			operation	fsue = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA
				T _A = +25°C	Resonator connection		4.4	6.2	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μA
				T _A = +50°C	Resonator connection		4.5	7.4	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA
			T _A = +70°C	Resonator connection		4.6	8.3	μA	
			fsue = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA	
				T _A = +85°C	Resonator connection		5.4	11.6	μA
		fsue = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA		
		T _A = +105°C	Resonator connection		7.1	21.0	μA		

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz
 - LS (low-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 8 MHz
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fil: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$ (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2 ^{Note 2}	HALT	HS (high-	fiH = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA
current Note 1		mode	speed main)		V _{DD} = 3.0 V		0.72	2.9	mA
NOLE I			mode ^{Note 7}	file = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA
					V _{DD} = 3.0 V		0.57	2.3	mA
				fıн = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA
					V _{DD} = 3.0 V		0.50	1.7	mA
			LS (low- speed main)	$f_{H} = 8 \text{ MHz}^{\text{Note 4}},$ $T_A = -40 \text{ to } +85^{\circ}\text{C}$	V _{DD} = 3.0 V		320	910	μA
			mode ^{Note 7}						
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
			speed main) mode ^{Note 7}	V _{DD} = 5.0 V	Resonator connection		0.50	2.0	mA
			mode	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.0	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	mA
				V _{DD} = 5.0 V	Resonator connection		0.30	1.08	mA
				f _{MX} = 10 MHz ^{Note 3} ,			0.24	1.02	mA
					Resonator connection		0.30	1.08	mA
			LS (low-	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		130	720	μA
mo		speed main) mode ^{Note 7}	V _{DD} = 3.0 V, T _A = -40 to +85°C	Resonator connection		170	760	μA	
	HS (high-	$f_{H} = 4 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		1.15	4.0	mA		
			speed main)	fpll = 64 MHz, fclk = 32 MHz	V _{DD} = 3.0 V		1.15	4.0	mA
			mode ^{Note 7}	$f_{IH} = 4 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.95	3.2	mA
				fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		0.95	3.2	mA
			Subsystem	fs∪в = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μA
			clock	$T_A = -40^{\circ}C$	Resonator connection		0.47	0.89	μA
			operation	fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μA
				T _A = +25°C	Resonator connection		0.52	0.89	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.41	1.90	μA
				T _A = +50°C	Resonator connection		0.60	2.09	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.54	2.80	μA
				T _A = +70°C	Resonator connection		0.73	2.99	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μA
				T _A = +85°C	Resonator connection		1.46	6.29	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μA
	IDD3 ^{Note 6} STOP T _A = -40°C		T _A = +105°C	Resonator connection		3.23	15.7	μA	
					0.18	0.50	μA		
mode $T_A = +25^{\circ}C$	T _A = +25°C				0.23	0.50	μA		
		Note 8	T _A = +50°C				0.27	1.70	μA
			T _A = +70°C				0.44	2.60	μA
			T _A = +85°C				1.17	5.90	μΑ
			T _A = +105°C				2.94	15.3	μΑ

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 32 MHz
 - LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz
 - 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL ^{Note 1}						0.20		μA
RTC operating current	IRTC Notes 1, 2, 3						0.02		μA
12-bit interval timer operating current	i⊤ Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	f⊩ = 15 kHz					0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion maximum speed					1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	ADREF ^{Note 1}		Low voltage mode, AVREFP = VDD = 3.0 V				75.0		μA
Temperature sensor operating current	ITMPS ^{Note 1}						75.0		μA
LVD operating current	ILVD ^{Notes 1, 7}						0.08		μA
Self- programming operating current	_{FSP} Notes 1, 8						2.50	12.2	mA
Programmable gain amplifier operating current	_{PGA} Note 9				AV _{REFP} = V _{DD} = 5.0 V AV _{REFP} = V _{DD} = 3.0 V		0.21 0.18	0.31 0.29	mA mA
Comparator operating current	ICMP ^{Note 10}	When one comp	parato	r channel is	$AV_{REFP} = V_{DD} = 5.0 V$ $AV_{REFP} = V_{DD} = 3.0 V$		41.4 37.2	62 59	μA
	IVREF	When one interr	nal ref	erence voltage	$AV_{REFP} = VDD = 5.0 V$ $AV_{REFP} = VDD = 5.0 V$		14.8	26	μA μA
	TURE	circuit is operati		oronoo vonago	$AV_{REFP} = V_{DD} = 3.0 V$		8.9	20	μA
Programmable	IIREF ^{Note 11}				$AV_{REFP} = V_{DD} = 5.0 V$		3.2	5.1	μA
gain amplifier/ comparator reference current source					AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μA
BGO operating current	I _{BGO} Note 12						2.50	12.2	mA
SNOOZE	Isnoz ^{Note 1}	ADC operation	n The mode is performed ^{Note 13}			0.50	1.1	mA	
operating current			The A/D conversion operations are performed, Standard mode, AV _{REFP} = V_{DD} = 5.0 V			2.0	3.04	mA	
		CSI/UART oper	ation				0.70	1.54	mA

(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to the VDD.

- 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fi∟ operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing during self-programming operation.
- **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
- **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
- **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
- 12. Current flowing only during data flash rewrite.
- 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode .

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- **2.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- **3.** fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is T_A = 25°C
- **5.** Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AV_{REFP} = V_{DD} = 5.0 V)

$$\begin{split} & \mathsf{ICMP} \times 3 + \mathsf{IVREF} + \mathsf{IPGA} + \mathsf{IREF} \\ &= 41.4 \ [\mu \mathsf{A}] \times 3 + 14.8 \ [\mu \mathsf{A}] \times 1 + 210 \ [\mu \mathsf{A}] + 3.2 \ [\mu \mathsf{A}] \\ &= 352.2 \ [\mu \mathsf{A}] \end{split}$$

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AV_{REFP} = V_{DD} = 5.0 V)

ICMP × 2 + IIREF = 41.4 [μA] × 2 + 3.2 [μA] = 86.0 [μA]

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2.4 AC Characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Items	Symbol		Conditio	ons		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main system	HS (high-spe	eed i	main) mode	0.03125		1	μs
instruction execution time)		clock (fmain) operation	LS (low-spee main) mode		T _A = -40 to +85°C	0.125		1	μs
		Subsystem clock (fsub) operation			28.5	30.5	31.3	μs	
		In the self	HS (high-spe	eed i	main) mode	0.03125		1	μs
		programming mode	programming LS (low-speed $T_A = -40$ to $+85^{\circ}C$		0.125		1	μS	
External system clock frequency	fex		•			1.0		20.0	MHz
	fexs			32		35	kHz		
External system clock input high-	texh, texl					24			ns
level width, low-level width	texns, texls					13.7			μS
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтн, tт∟					2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	fто	HS (high-spee	d main)	4.($V \leq V_{\text{DD}} \leq 5.5 \text{ V}$			8	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to		mode		2.7	$7 \text{ V} \le \text{V}_{\text{DD}}$ < 4.0 V			4	MHz
TKCO05 output frequency (When duty = 50%)		LS (low-speed		4.($V \leq V_{\text{DD}} \leq 5.5 \text{ V}$			4	MHz
(when duty = 00 %)		mode, $I_A = -4$	mode, $T_A = -40$ to +85°C 2.7 V $\leq V_{DD} < 4.0$ V				2	MHz	
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23		1			μs		
RESET low-level width	trsl				10			μs	

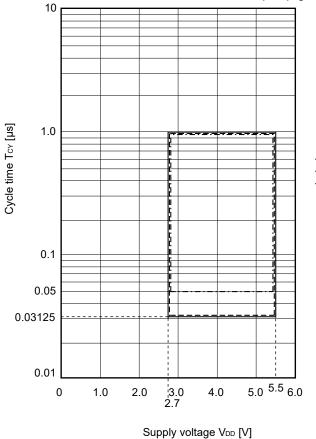
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



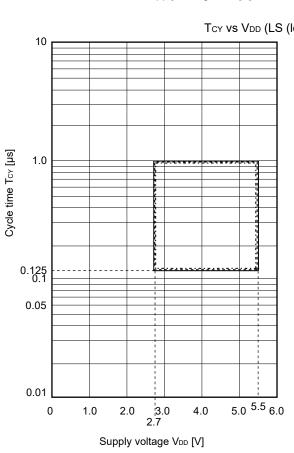
Minimum Instruction Execution Time during Main System Clock Operation





When the high-speed on-chip oscillator clock is selected ___

During self programming When high-speed system clock is selected _ . _ .

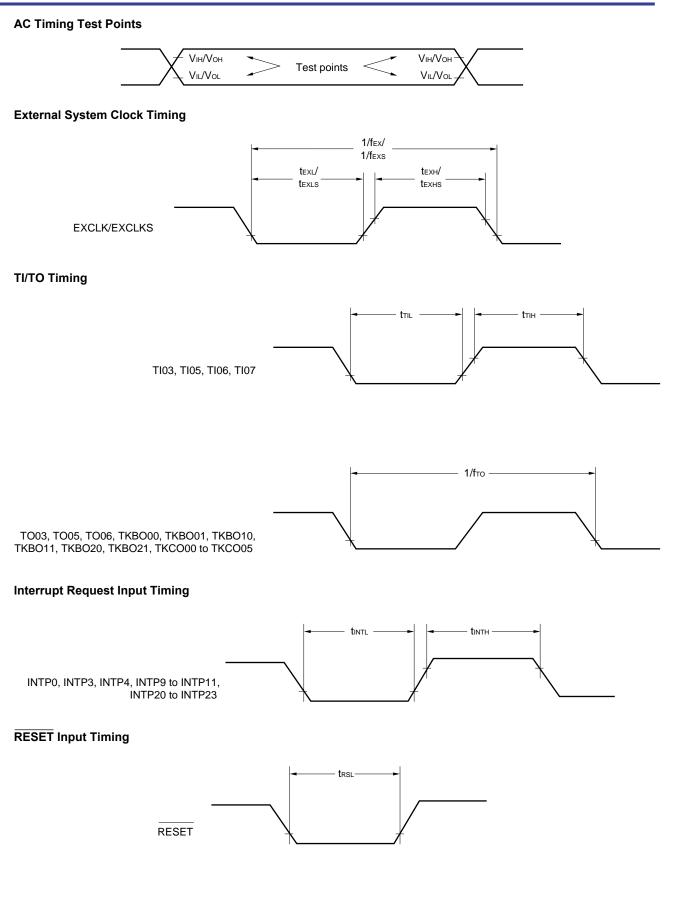


TCY vs VDD (LS (low-speed main) mode)

When the high-speed on-chip oscillator clock is selected

--- During self programming When high-speed system clock is selected

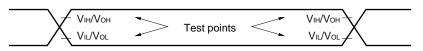






2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode) $(T_A = -40 \text{ to } +105^\circ\text{C}, \ 2.7 \text{ V} \le V_{\text{DD}} \le 5.5 \text{ V}, \ \text{Vss} = 0 \text{ V})$

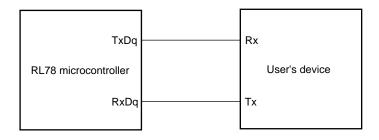
Parameter	Symbol		Conditions		Conditions HS		peed main) ode	LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.			
Transfer rate ^{Note 1}		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$	$2.7 \text{ V}{\leq} \text{V}_{\text{DD}}{\leq} 5.5 \text{ V}$		fмск/6		fмск/6	bps		
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps		

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

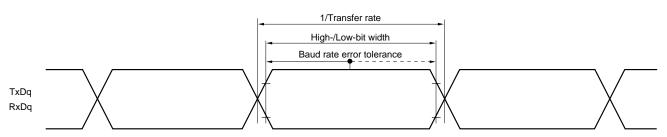
2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are: HS (high-speed main) mode: 32 MHz (2.7 V \leq V_{DD} \leq 5.5 V) LS (low-speed main) mode: 8 MHz (2.7 V \leq V_{DD} \leq 5.5 V), T_A = -40 to +85°C

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_A = -40$ to $+105^{\circ}C^{Note 5}$, 2.7 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-sp Mo	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fclк	125		500		ns
SCKp high-/low-level	tкнı,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	tксү1/2 – 12		tксү1/2 – 50		ns
width	t ĸ∟1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	tксү1/2 – 18		tксү1/2 – 50		ns
SIp setup time (to SCKp \uparrow)	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	44		110		ns
Note 1		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	44		110		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi1		19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** C is the load capacitance of the SCKp and SOp output lines.
- **5.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 - g: PIM and POM number (g = 1)
 - 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}C^{\text{Note 6}}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Condit	ions		peed main) ode	LS (low-spee	d main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү2	$4.0~V \leq V_{DD} \leq 5.5~V$	20 MHz < fмск	8/fмск		_		ns
Note 5			fмск \leq 20 MHz	6/fмск		6/fмск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	8/fмск		-		ns
			fмск \leq 16 MHz	6/fмск		6/fмск		ns
SCKp high-/low- level width	tкн2, tкL2			tксү2/2		tксү2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik2			1/fмск+20		1/fмск+30		ns
Slp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+31		1/fмск+31		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso2	C = 30 pF ^{Note 4}			2/f _{мск} + 44		2/f _{мск+} 110	ns

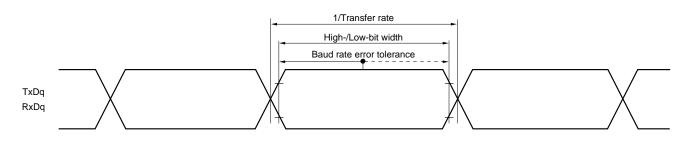
- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - **6.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - 2. fmck: Serial array unit operation clock frequency

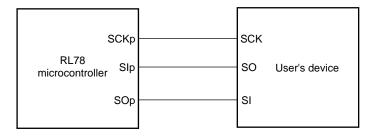
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

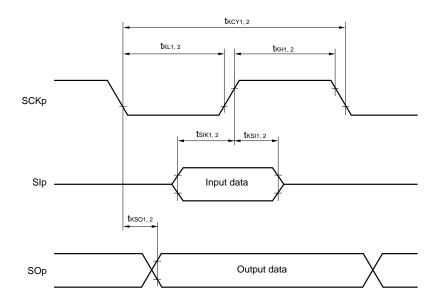




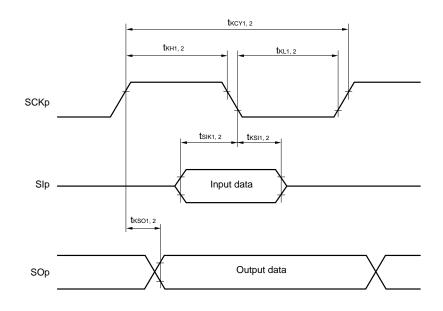
CSI mode connection diagram (during communication at same potential)

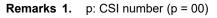


CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)





2. m: Unit number, n: Channel number (mn = 00)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit	
					MIN.	MAX.	MIN.	MAX.	
Transfer		Reception	4.0 V	$\leq V_{\text{DD}} \leq 5.5~\text{V},~2.7~\text{V} \leq V_{\text{b}} \leq 4.0~\text{V}$		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps
rate				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps
			2.7 V	\leq V_{DD} < 4.0 V, 2.3 V \leq V_b \leq 2.7 V		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$ LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$, TA = -40 to +85°C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2) ($T_A = -40$ to $+105^{\circ}C^{Note 5}$, 2.7 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol			Conditions		h-speed Mode	· ·	beed main) bde	Unit
					MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V	$\leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{\text{b}} \leq 4.0~V$		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
			2.7 V	$\leq V_{\text{DD}}$ < 4.0 V, 2.3 V $\leq V_{\text{b}} \leq$ 2.7 V		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. See Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_DD < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \text{ [%]}$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- 5. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

 $C_{b}[F]: \mbox{ Communication line (TxDq) load capacitance, V_{b}[V]: \mbox{ Communication line voltage}$

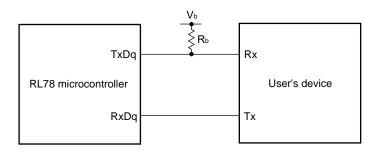
- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

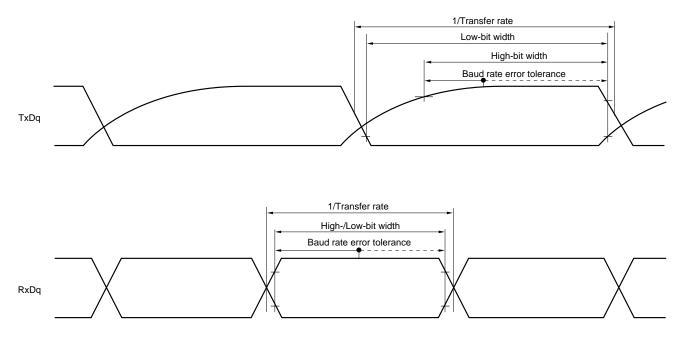
m: Unit number, n: Channel number (mn = 00 to 03))



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, V_b[V]: Communication line voltage
 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)



(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note 3}}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high main) I	•	LS (low-s main) M	•	Unit
				MIN.	MAX.	MIN.	MAX.	ĺ
SCKp cycle time	tkcy1	tксү1 ≥ 2/f с∟к		200		1150		ns
			$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{\text{DD}} < 4.0 \; \text{V}, \; 2.3 \; V \leq V_{\text{b}} \leq 2.7 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 2.7 \; \text{k}\Omega \end{array}$	300		1150		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{f} \end{array}$	5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	tксү1/2 – 50		tkcy1/2 – 75		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < \\ C_b = 30 \ pF, \ F \end{array}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k\Omega	tксү1/2 – 120		tксү1/2 – 170		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	$ 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}, $ R _b = 1.4 kΩ	tксү1/2 – 7		tkcy1/2 – 50		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k\Omega	tксү1/2 – 10		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	$\label{eq:2.5} \begin{array}{l} 5.5 \mbox{ V, } 2.7 \mbox{ V} \leq V_b \leq 4.0 \mbox{ V,} \\ R_b = 1.4 k\Omega \end{array}$	81		479		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$ 4.0 V, 2.3 V \le V_b \le 2.7 V, $ R _b = 2.7 kΩ	177		479		ns
Slp hold time (from SCKp↑)	tksi1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF}, \text{ F}$: 5.5 V, 2.7 V \leq V_b \leq 4.0 V, R_b = 1.4 $k\Omega$	10		19		ns
Note 1		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ C _b = 30 pF, F	$ 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}, $ R _b = 2.7 kΩ	10		19		ns
Delay time from SCKp↓ to SOp	tkso1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF, F}$	$ 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}, $ R _b = 1.4 kΩ		60		100	ns
output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{\text{DD}} \le C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$x 4.0 V, 2.3 V \le V_b \le 2.7 V,$ R _b = 2.7 kΩ		130		195	ns
Slp setup time (to SCKp↓) ^{Note 2}	tsik1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$ 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}, $ R _b = 1.4 kΩ	44		110		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$ 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}, $ R _b = 2.7 kΩ	44		110		ns
Slp hold time (from SCKp↓)	tksı1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$ 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}, $ R _b = 1.4 kΩ	10		19		ns
Note 2		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$x 4.0 V, 2.3 V \le V_b \le 2.7 V,$ R _b = 2.7 kΩ	10		19		ns
Delay time from SCKp↑ to	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	$\label{eq:states} \begin{array}{l} 5.5 \mbox{ V}, \mbox{ 2.7 } \mbox{ V} \leq \mbox{ V}_b \leq \mbox{ 4.0 } \mbox{ V}, \\ R_b = 1.4 \Omega \end{array}$		10		25	ns
SOp output ^{Note 2}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$x 4.0 V$, 2.3 V \le V _b \le 2.7 V, R _b = 2.7 kΩ		10		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note 3}}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	d main) Mode	LS (low-speed	d main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксүı	tĸcy1 ≥ 4/fc∟ĸ		300		1150		ns
			$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		1150		ns
SCKp high-level width	t кн1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_{b} \leq 4.0$ V, R_b = 1.4 k\Omega	tксү1/2 — 75		tксү1/2 – 75		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_{b} = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k\Omega	tксү1/2 – 170		tксү1/2 – 170		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	\leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, R _b = 1.4 kΩ	tксү1/2 – 12		tксү1/2 – 50		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	tксү1/2 – 18		tксү1/2 – 50		ns
SIp setup time (to SCKp↑) Note 1	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	81		479		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	177		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	19		19		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_{\rm b} = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega		100		100	ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ		195		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$ R _b = 1.4 kΩ	44		110		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	44		110		ns
SIp hold time (from SCKp↓)	tksi1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \\ \text{Cb} = 30 \ \text{pF}, \end{array}$	\leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, Rb = 1.4 kΩ	19		19		ns
			< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, Rb = 2.7 kΩ	19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1		≤ 5.5 V, 2.7 V $\leq V_{b} \leq 4.0$ V, Rb = 1.4 k\Omega		25		25	ns
SOp output			< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, Rb = 2.7 kΩ		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

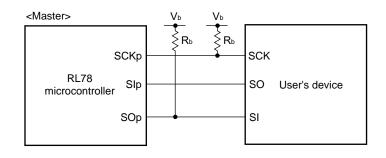
3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

(Caution and Remarks are listed on the next page.)



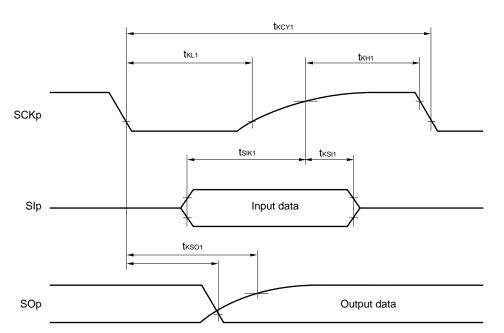
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

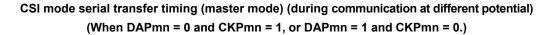


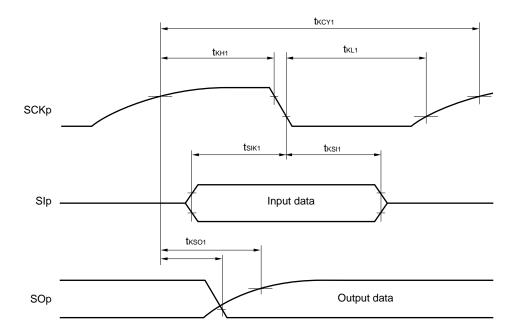
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



(7) DALI/UART4 mode

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		peed main) ode	LS (low-sp Mo	oeed main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/12		fмск/12	bps
		Maximum transfer rate theoretical value HS: fcLk = 32 MHz, fMCk = fcLk LS: fcLk = 8 MHz, fMCk = fcLk		2.6		0.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.



2.5.2 Serial interface IICA

(1) I²C standard mode

$(T_A = -40 \text{ to } +105^{\circ}C^{\text{Note 3}}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	、 Ŭ	h-speed Mode		/-speed Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: $f_{CLK} \ge 1 \text{ MHz}$	0	100	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		4.7		μs
Hold time ^{Note 1}	thd:sta		4.0		4.0		μs
Hold time when SCLA0 = "L"	tLOW		4.7		4.7		μs
Hold time when SCLA0 = "H"	tніgн		4.0		4.0		μs
Data setup time (reception)	tsu:dat		250		250		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	3.45	μs
Setup time of stop condition	tsu:sto		4.0		4.0		μs
Bus-free time	t BUF		4.7		4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of the control transfer and a wait state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω



(2) I²C fast mode

$(T_A = -40 \text{ to } +105^{\circ}C^{\text{ Note } 3}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

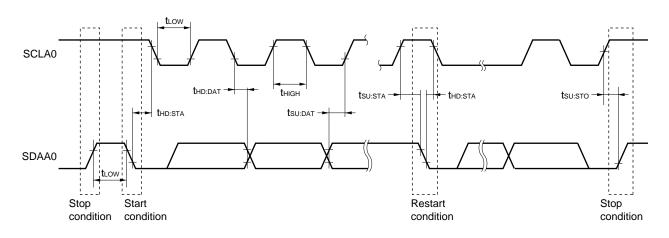
Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	fast mode: fcLK \ge 3.5 MHz	0	400	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		0.6		μS
Hold time ^{Note 1}	thd:sta		0.6		0.6		μS
Hold time when SCLA0 = "L"	t∟ow		1.3		1.3		μS
Hold time when SCLA0 = "H"	tніgн		0.6		0.6		μS
Data setup time (reception)	tsu:dat		100		100		ns
Data hold time (transmission)Note 2	thd:dat		0	0.9	0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		0.6		μS
Bus-free time	t BUF		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω

IICA serial transfer timing





2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 2.6.1 (1).	See 2.6.1 (3) .	See 2.6.1 (4).
ANI16 to ANI19	See 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	See 2.6.1 (1) .		_



(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = $V_{DD}^{Note 3}$			1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
		10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	Vain	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		VBGR ^{Note 4}		V
		Temperature sensor output v (HS (high-speed main) mode	0	Ň	/TMPS25 ^{Note}	4	V

Notes 1. Excludes quantization error (±1/2 LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD.}

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



- (2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19
- $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}			1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Integral linearity error ^{Note} 1	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AVREFP and VDD	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.



(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	7	0		VDD	V
		ANI16 to ANI19		0		Vdd	V
		Internal reference voltage (HS (high-speed main) mod	e)		VBGR ^{Note 3}		V
		Temperature sensor output (HS (high-speed main) mod	0	Ň	/ _{TMPS25} Note	3	V

$(T_A = -40 \text{ to } +105^{\circ}\text{C} 2.7 \text{ V} \le \text{Vpp} \le 5.5$	V, Vss = 0 V, Reference voltage (+) = VDD	Reference voltage $(-) = V_{SS}$
$(1A40 10 + 105 C, 2.7 V \le VDD \le 5.5$	v, vss – v v, relefence vollage (+) – vou	, Reference vollage ($-$) – vss)

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage
 (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

 $⁽T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ V}_{\text{SS}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{\text{BGR}^{\text{Note 3}}}, \text{ Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V}^{\text{Note 4}}, \text{ HS (high-speed main) mode)}$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	t CONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



2.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	VBGRT	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)



2.6.3 Programmable gain amplifier

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9Vdd/	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	s				±1.5	%
		32 time	s				±2	%
Slew rate ^{Note 1}	SRRPGA	Rising edge	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	4, 8 times	4			V/µs
	edge			16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.8			V/µs
				16, 32 times	0.5			V/µs
	SRFPGA	Falling	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	4, 8 times	3.2			V/µs
		edge	dge	16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.2			V/µs
				16, 32 times	0.5			V/µs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 tim	es		5			μs
		16, 32 t	imes		10			μS

(TA = -40 to +105°C, 2.7 V \leq AVREFP = Vdd \leq 5.5 V, Vss = AVREFM = 0 V)

Notes 1. When $V_{IPGA} = 0.1V_{DD}/gain$ to $0.9V_{DD}/gain$.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

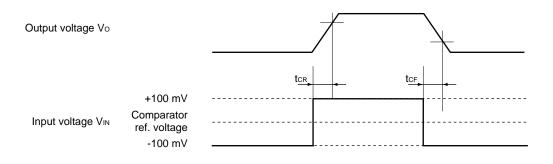


2.6.4 Comparator

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		Vdd	V
		СМРСОМ	0.045		0.9Vdd	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3~V \leq V_{\text{DD}} \leq 5.5~V$	1			μs
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	3			μs
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μS

(TA = -40 to +105°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, VSS = AVREFM = 0 V)

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.
- **Remark** These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.



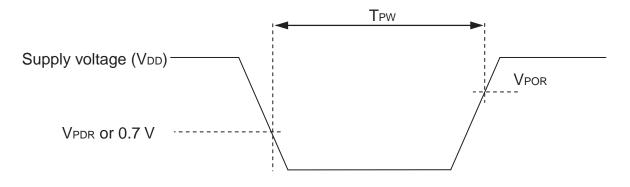


2.6.5 POR circuit characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	VPDR	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.97	4.06	4.14	V
voltage			Power supply fall time	3.89	3.98	4.06	V
		VLVD1	Power supply rise time	3.67	3.75	3.82	V
			Power supply fall time	3.59	3.67	3.74	V
		VLVD2	Power supply rise time	3.06	3.13	3.19	V
			Power supply fall time	2.99	3.06	3.12	V
		VLVD3	Power supply rise time	2.95	3.02	3.08	V
			Power supply fall time	2.89	2.96	3.02	V
		VLVD4	Power supply rise time	2.85	2.92	2.97	V
			Power supply fall time	2.79	2.86	2.91	V
		VLVD5	Power supply rise time	2.75	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pul	se width	tLW		300			μS
Detection de	lay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1,	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage: 2.7 V			2.81	V
mode	VLVD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	2.97	V
			Falling interrupt voltage	2.79	2.86	2.91	V
	VLVD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.08	V
			Falling interrupt voltage	2.89	2.96	3.02	V
	VLVD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.14	V
			Falling interrupt voltage	3.89	3.98	4.06	V

2.6.7 Supply voltage rise inclination characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 32.4 AC Characteristics.

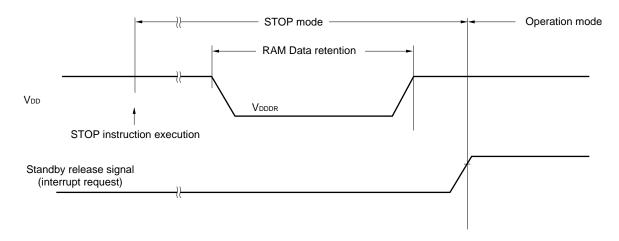


2.7 RAM Data Retention Characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage ^{Note 2}	VDDDR		1.44 ^{Note 1}		5.5	V

- **Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.





2.8 Flash Memory Programming Characteristics

(
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.				
CPU/peripheral hardware clock frequency	fclĸ	$2.7~V \leq V \text{dd} \leq 5.5~V$	1		32				
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3}	1,000						
Number of data flash		Retained for 1 year, $T_A = 25^{\circ}C^{Note 3}$		1,000,000					
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, $T_A = 85^{\circ}C^{Note 3}$	100,000						
		Retained for 20 years, $T_A = 85^{\circ}C^{Note 3}$	10,000						

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- 2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps



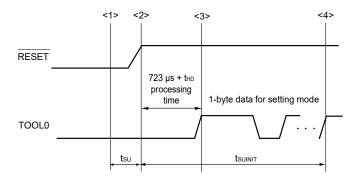
Unit MHz

Times

2.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +105^{\circ}\text{C})$	$2.7 V \le V_{DD} \le 5.5 V, V_{SS} = 0 V$
(IA 40.00 0,	, 2 • 3 • 66 3 • 6 • 7

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	ts∪	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tнD	POR and LVD reset must end before the external reset ends.	1			ms



<R>

- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)



3. ELECTRICAL SPECIFICATIONS (M: Industrial applications, $T_A = -40$ to +125°C)

In this chapter, shows the electrical specifications of the target products. Target products (M: Industrial applications): $T_A = -40$ to $+125^{\circ}C$ R5F107xxMxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.
 - 3. When any of these products are used at 105°C or lower, see 2. ELECTRICAL SPECIFICATIONS $(T_A = -40 \text{ to } +105^{\circ}\text{C}).$



3.1 Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VI1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	–0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Vai1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

Absolute Maximum Ratings (T_A = 25°C) (1/2)

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF(+)}$: + side reference voltage of the A/D converter.
 - **3.** Vss : Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins –170 mA	P02, P03, P40, P120	-70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	IOL2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +125	°C
temperature		In flash memory	programming mode	-40 to +105	
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (T_A = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator		1.0		20.0	MHz
XT1 clock frequency (f _{XT}) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.



3.2.2 On-chip oscillator characteristics

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator		T _A = −20 to 85°C	-1		+1	%
clock frequency accuracyNote 2		T _A = −40 to 105°C	-1.5		+1.5	%
		T _A = –40 to 125°C When 16 MHz selected	-2		+2	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

 $(T_A = -40 \text{ to } +125^{\circ}C, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.
- **Remark** When using the device at an ambient temperature that exceeds T_A = 105°C, the selectable oscillation frequency is 16 MHz max.

3.2.3 PLL characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f _{MX} = 4 MHz)	3.92	4.00	4.08	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected ($f_{IH} = 4 \text{ MHz}$)	3.92	4.00	4.08	MHz
PLL output clock frequency ^{Note}	fpll			$f_{\text{PLLIN}} imes 16$		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105^{\circ}C$, only 16 MHz (f_{PLL} × 1/4) can be selected as the CPU operating frequency.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-9.0	mA
	(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-3.0	mA	
	Total of P05, P06, P10 to P12, P30, P31,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-21.0	mA	
		P75 to P77, P147, P200 to P206 (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-6.0	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-21.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-9.0	mA
	Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.4	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	IOL1	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			8.5 ^{Note 2}	mA
low ^{Note 1}	P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			1.5 ^{Note 2}	mA	
	Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			20.0	mA	
	(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			5.0	mA	
		Total of P05, P06, P10 to P12, P30, P31,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			20.0	mA
		P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$			10.0	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			15.0	mA
	IOL2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			1.6	mA

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	Vih1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	2.1		Vdd	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
			TTL input buffer 2.7 V \leq V_DD $<$ 3.3 V	1.5		Vdd	V
Input voltage, low VIL1		P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	VIL2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $2.7~V \leq V_{\text{DD}} < 3.3~V$	0		0.32	V

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Caution The maximum value of V_{IH} of pins P02, P10 to P12 is V_{DD}, even in the N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, Vон1 high		P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ \text{mA} \end{array}$	Vdd - 0.7			V
	P200 to P206	$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -1.0 \ \text{mA} \end{array} \end{array}$	Vdd - 0.5			V	
	V _{0H2} P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh2 = -100 μ A	Vdd - 0.5			V	
Output voltage, V _{OL1} low		P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:DD}$			0.7	V
	P200 to P206	P200 to P206	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 4.0 mA			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 1.5 mA			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol2 = 400 μ A			0.4	V

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Condition	IS		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	Vi = V _{DD}				1	μA
	Ilih2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	11.11	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = VSS				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	Vı = Vss, li	n input port	10	20	100	kΩ

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)



3.3.2 Supply current characteristics

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	f⊮ = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.8	mA
Current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		2.9	4.8	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.7	mA
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.7	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA
				V _{DD} = 5.0 V	Resonator connection		2.0	3.3	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA
		V _{DD} = 3.0 V	Resonator connection		2.0	3.3	mA		
			HS (high-	f⊪ = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	6.5	mA
		speed main) fPLL = 64 MHz, mode ^{Note 5}	fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		3.3	6.5	mA	
			Subsystem clock $f_{SUB} = 32.768 \text{ kHz}^{Note 4}$ $T_A = -40^{\circ}\text{C}$ operation $f_{SUB} = 32.768 \text{ kHz}^{Note 4}$	$T_A = -40^{\circ}C$	Square wave input		4.2	6.0	μA
					Resonator connection		4.4	6.2	μA
				Square wave input		4.2	6.0	μA	
				T _A = +25°C	Resonator connection		4.4	6.2	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μA
				T _A = +50°C	Resonator connection		4.5	7.4	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA
				T _A = +70°C	Resonator connection		4.6	8.3	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA
				T _A = +85°C	Resonator connection		5.4	11.6	μA
			fsue = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA	
				T _A = +105°C	Resonator connection		7.1	21.0	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		11.1	51.2	μA
				T _A = +125°C	Resonator connection		11.3	51.4	μA

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 20 MHz
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit	
Supply current Note 1	IDD2 ^{Note 2}	HALT mode	HS (high- speed main) mode ^{Note 7}	f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.0	mA
					V _{DD} = 3.0 V		0.50	2.0	mA
			HS (high- speed main) mode ^{Note 7}	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 5.0 \text{ V}$	Square wave input		0.40	2.2	mA
					Resonator connection		0.50	2.3	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Square wave input		0.40	2.2	mA
					Resonator connection		0.50	2.3	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 5.0 \text{ V}$	Square wave input		0.24	1.22	mA
					Resonator connection		0.30	1.28	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Square wave input		0.24	1.22	mA
					Resonator connection		0.30	1.28	mA
			HS (high- speed main) mode ^{Note 7}	f_{H} = 4 MHz ^{Note 4} f_{PLL} = 64 MHz, f_{CLK} = 16 MHz	V _{DD} = 5.0 V		0.95	3.7	mA
					V _{DD} = 3.0 V		0.95	3.7	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = -40°C	Square wave input		0.28	0.70	μA
					Resonator connection		0.47	0.89	μA
				fsub = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.33	0.70	μA
					Resonator connection		0.52	0.89	μA
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	1.90	μA
					Resonator connection		0.60	2.09	μA
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μA
					Resonator connection		0.73	2.99	μA
				fs∪b = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.27	6.10	μA
					Resonator connection		1.46	6.29	μA
				fsuв = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		3.04	15.5	μA
					Resonator connection		3.23	15.7	μA
				f _{S∪B} = 32.768 kHz ^{Note 5} T _A = +125°C	Square wave input		7.20	45.2	μA
					Resonator connection		7.53	45.5	μA
	I _{DD3} Note 6	STOP mode Note 8	$T_A = -40^{\circ}C$				0.18	0.50	μA
			T _A = +25°C				0.23	0.50	μA
			T _A = +50°C				0.27	1.70	μA
			T _A = +70°C				0.44	2.60	μA
			T _A = +85°C				1.17	5.90	μA
			T _A = +105°C	T _A = +105°C			2.94	15.3	μA
			T _A = +125°C				7.14	45.1	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - **2.** During HALT instruction execution by flash memory.
 - **3.** When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 20 MHz
 - 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



Parameter	Symbol		Conditio	ns	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	_{FIL} Note 1					0.20		μA
RTC operating current	IRTC Notes 1, 2, 3					0.02		μA
12-bit interval timer operating current	i⊤ Notes 1, 2, 4					0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	fı∟ = 15 kHz				0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion maximum spee	When conversion at Normal mode, AVREFP = VDD = 5.0 V naximum speed			1.3	1.7	mA
A/D converter reference voltage current	ADREF ^{Note 1}					75.0		μA
Temperature sensor operating current	I _{TMPS} Note 1					75.0		μA
LVD operating current	LVD ^{Notes 1, 7}					0.08		μA
Self-programming operating current	_{FSP} Notes 1, 8					2.5	12.2	mA
Programmable	IPGA ^{Note 9}			AV _{REFP} = V _{DD} = 5.0 V		0.21	0.37	mA
gain amplifier operating current				$AV_{REFP} = V_{DD} = 3.0 V$		0.18	0.35	mA
Comparator	ICMP ^{Note 10}	When one com	parator channel is	$AV_{REFP} = V_{DD} = 5.0 V$		41.4	74	μA
operating current		operating		$AV_{REFP} = V_{DD} = 3.0 V$		37.2	71	μA
	IVREF	When one inter	nal reference voltag	e AV _{REFP} = V _{DD} = 5.0 V		14.8	31	μA
		circuit is operat	ng	$AV_{REFP} = V_{DD} = 3.0 V$		8.9	24	μA
Programmable	IREF ^{Note 11}			$AV_{REFP} = V_{DD} = 5.0 V$		3.2	6.1	μA
gain amplifier/ comparator reference current source				AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μA
BGO operating current	BGO ^{Note 12}					2.50	12.2	mA
SNOOZE	Isnoz ^{Note 1}	A/D converter	The mode is perfo	med ^{Note 13}		0.50	1.10	mA
operating current		operation	· · · · · · · · · · · · · · · · · · ·			1.20	2.17	mA
		CSI/UART operation				0.70	1.27	mA

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to the VDD.

- 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and f_{IL} operating current). The current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IWDT, when the watchdog timer is operating.
- **6.** Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, when the A/D converter is operating in operating mode or in HALT mode.
- **7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing during self-programming operation.
- **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
- **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
- **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
- 12. Current flowing only during data flash rewrite.
- 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is T_A = 25°C
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AV_{REFP} = V_{DD} = 5.0 V)

ICMP × 3 + IVREF + IPGA + IREF

 $= 41.4 \ [\mu A] \times 3 + 14.8 \ [\mu A] \times 1 + 210 \ [\mu A] + 3.2 \ [\mu A]$ $= 352.2 \ [\mu A]$

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AV_{REFP} = V_{DD} = 5.0 V)

 $I_{CMP} \times 2 + I_{IREF}$ = 41.4 [μ A] × 2 + 3.2 [μ A] = 86.0 [μ A]



3.4 AC Characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсү	Main system clock (f _{MAIN}) operation	HS (high-s	peed n	nain) mode	0.05		1	μs
		Subsystem c	Subsystem clock (fsub) operation			28.5	30.5	31.3	μs
		In the self programming mode	HS (high-s main) mod	•	T _A = -40 to +105°C	0.05		1	μs
External system clock frequency	f _{EX}					1.0		20.0	MHz
	fexs					32		35	kHz
External system clock input high- level width, low-level width	texн, texL				24			ns	
	texns, texus				13.7			μS	
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтıн, tтı∟					2/fмск+10			ns
T003, T005, T006, TKB000,	fто	HS (high-speed main)		4.0 \	$V \le V_{\text{DD}} \le 5.5 \text{ V}$			5	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)		mode		2.7 \	$V \le V_{DD} < 4.0 V$			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3 INTP9 to INT INTP20 to IN	P11,	2.7 \	$V \le V_{DD} \le 5.5 V$	1			μS
RESET low-level width	trsl					10			μs

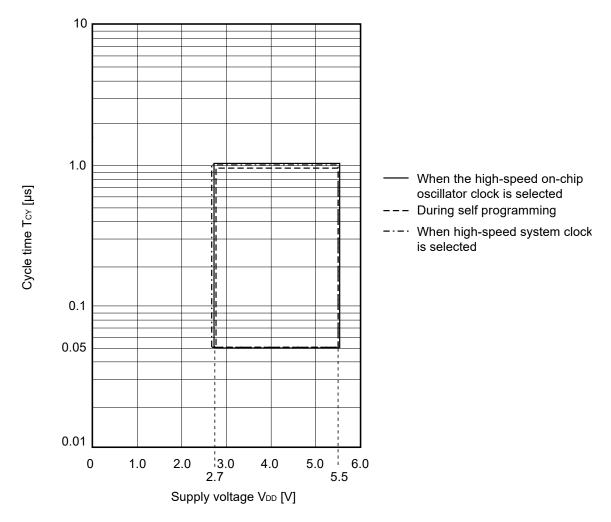
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

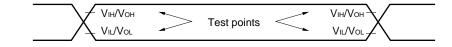


Minimum Instruction Execution Time during Main System Clock Operation

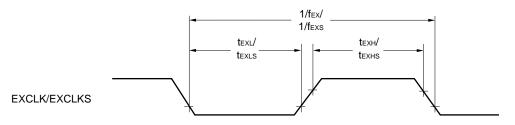
TCY VS VDD (HS (high-speed main) mode)



AC Timing Test Points

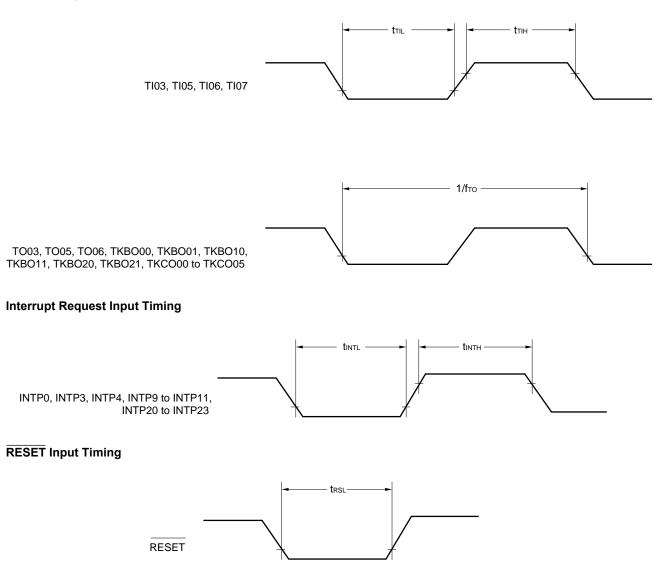


External System Clock Timing





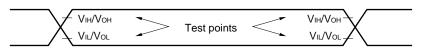
TI/TO Timing





3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode)

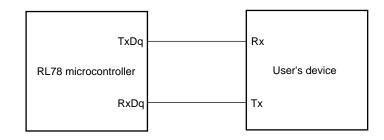
(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		Conditions HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate ^{Note 1}					fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

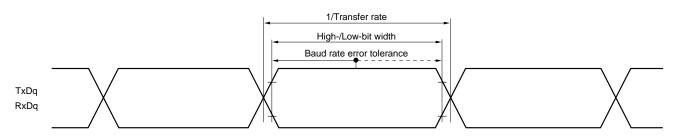
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: 20 MHz ($2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$)

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_A = -40$ to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		DI Conditions HS (high-speed main) Mode		,	Unit
				MIN.	MAX.		
SCKp cycle time	tkCY1	$t_{KCY1} \geq 4/f_{CLK}$	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	250		ns	
			$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	500		ns	
SCKp high-/low-level width	tkh1, $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		V	tксү1/2 – 20		ns	
	t _{KL1}	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tkcy1/2 - 40		ns	
SIp setup time (to SCKp↑) ^{Note 1}	tsiĸ1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V_{\text{DD}}$	V	80		ns	
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		80		ns	
SIp hold time (from SCKp↑) ^{Note 2}	tksi1			40		ns	
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}			80	ns	

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), q: PIM and POM number (g = 1)
 - 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to +125°C, 2.7 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	fмск ≤ 20 MHz	6/fмск		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	8/fмск		ns
			fмск ≤ 16 MHz	6/fмск		ns
SCKp high-/low-level width	tкн2, tкL2			tксү2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsiк2			1/fмск+40		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+60		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tĸso2	C = 30 pF ^{Note 4}			2/fмск+80	ns

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

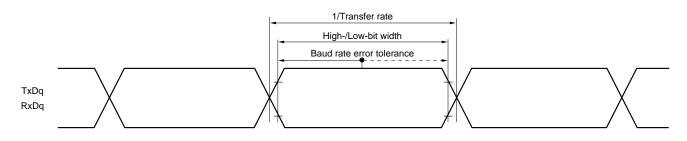
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

2. fmck: Serial array unit operation clock frequency

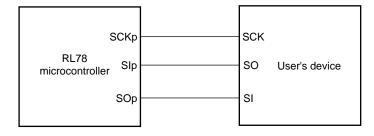
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

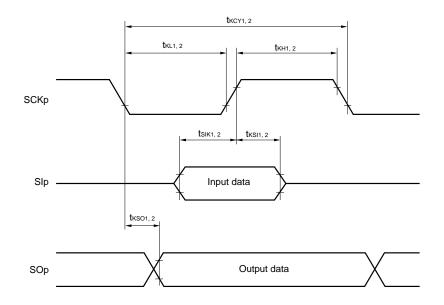




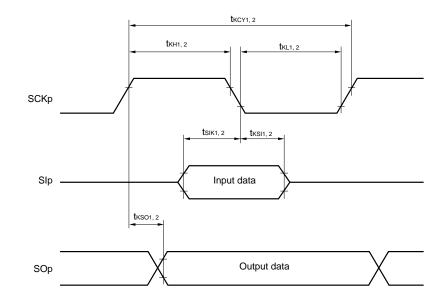
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Conditions				Unit
					MIN.	MAX.	
Transfer rate		Reception	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V \end{array}$			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2) (T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (hig main)	Unit			
					MIN.	MAX.			
Transfer rate		Transmission	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,$			Note 1	bps		
		Theoretical va	$2.7~V \leq V_b \leq 4.0~V$	$2.7~V \leq V_b \leq 4.0~V$	$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.8 ^{Note 2}	Mbps
			$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V},$			Note 3	bps		
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 ^{Note 4}	Mbps		

Notes 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq Vpd < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

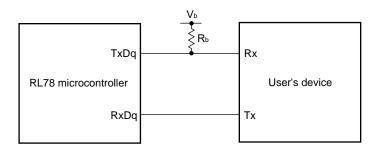
- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- **3.** fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

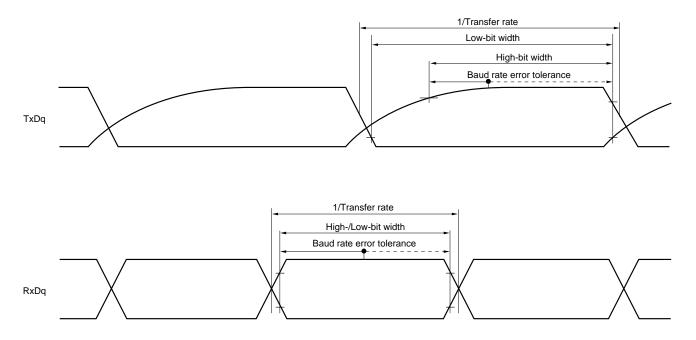
m: Unit number, n: Channel number (mn = 00 to 03))



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, V_b[V]: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)



(5) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) ($T_A = -40$ to +125°C, 2.7 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-sp Mo	-	Unit
				MIN.	MAX.	
SCKp cycle time	t ксү1	tксү1 ≥ 4/fclк		600		ns
			$\label{eq:VDD} \begin{split} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1000		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$: 5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	tксү1/2 – 80		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < \\ C_b = 30 \ pF, \ F \end{array}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	tксү1/2 – 170		ns
SCKp low-level width tkL1		$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	$\label{eq:states} \begin{array}{l} 5.5 \mbox{ V}, \mbox{ 2.7 } \mbox{ V} \leq V_b \leq 4.0 \mbox{ V}, \\ R_b = 1.4 k\Omega \end{array}$	tkcy1/2 - 28		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		t _{KCY1} /2-40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıkı	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_{b} = 30 \ pF, \ F \end{array}$	± 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, Rb = 1.4 k\Omega	160		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k\Omega	250		ns
SIp hold time (from SCKp↑) ^{Note 1}	$\label{eq:ksin} t_{\text{KSI1}} \qquad \qquad 4.0 \ \text{V} \leq \text{V}_{\text{DD}} \\ C_{\text{b}} = 30 \ \text{pF},$: 5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	40		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < \\ C_b = 30 \ pF, \ F \end{array}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	40		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	\pm 5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega		160	ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω		250	ns
Slp setup time (to SCKp↓) ^{Note 2}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$: 5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	80		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	80		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksıı	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$: 5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	40		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ C_{b} = 30 pF, F	: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	40		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	5.5 V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega		80	ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω		80	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

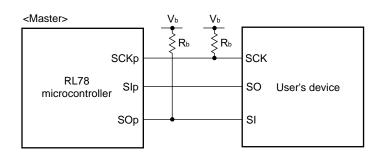
2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)



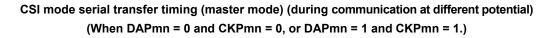
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

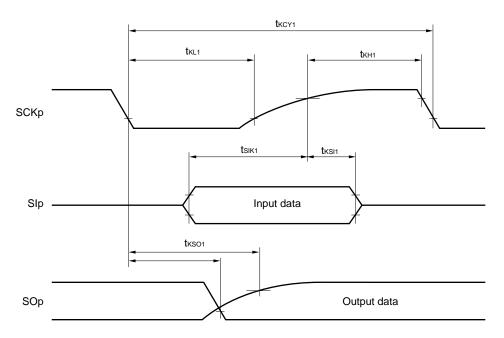
CSI mode connection diagram (during communication at different potential)

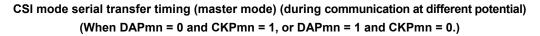


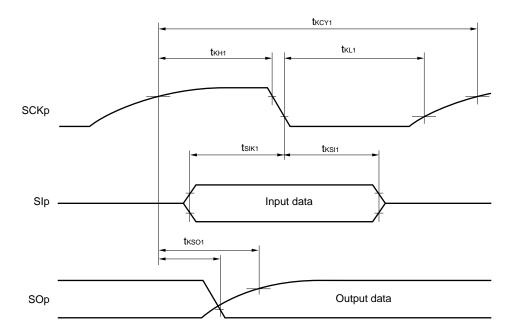
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)











- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



(6) DALI/UART4 mode

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate				fмск/12	bps
		Maximum transfer rate theoretical value f _{CLK} = 20 MHz, f _{MCK} = f _{CLK}		1.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register 4 (SPS4).)



3.5.2 Serial interface IICA

(1) I²C standard mode

$(T_A = -40 \text{ to } +125^{\circ}C, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLK≥ 1 MHz	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		μs
Hold time ^{Note 1}	thd:sta		4.0		μs
Hold time when SCLA0 = "L"	tLow		4.7		μs
Hold time when SCLA0 = "H"	tніgн		4.0		μs
Data setup time (reception)	tsu:dat		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	μs
Setup time of stop condition	tsu:sto		4.0		μs
Bus-free time	t BUF		4.7		μs

- **Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω



(2) I²C fast mode

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

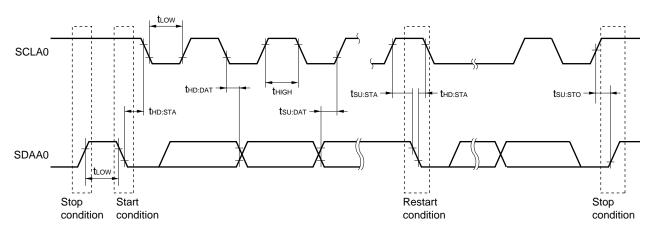
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: $f_{CLK} \ge 3.5 \text{ MHz}$	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		μs
Hold time ^{Note 1}	thd:sta		0.6		μs
Hold time when SCLA0 = "L"	tLOW		1.3		μs
Hold time when SCLA0 = "H"	tніgн		0.6		μs
Data setup time (reception)	tsu:dat		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	0.9	μs
Setup time of stop condition	tsu:sto		0.6		μs
Bus-free time	t BUF		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

fast mode:

 C_b = 320 pF, R_b = 1.1 k Ω



IICA serial transfer timing



Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 3.6.1 (1) .	See 3.6.1 (3).	See 3.6.1 (4) .
ANI16 to ANI19	See 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	See 3.6.1 (1) .		_



(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ V}_{\text{SS}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{ Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V}$

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = $V_{DD}^{Note 3}$			1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.4		39	μs
		10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \le V_{DD} \le 5.5~V$	3.8		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		VBGR ^{Note 4}		V
		Temperature sensor output v (HS (high-speed main) mode	0	N	VTMPS25 ^{Note}	4	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq AV _{REFP} \leq V _{DD} \leq 5.5 V, V _{SS} = 0 V, Reference voltage (+) = AV _{REFP} , AV _{REFP} , AV _{REFP} , AV _{REFP} , AV	;e
voltage (–) = AV _{REFM} = 0 V)	

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} < 5.5~V$	3.4		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP} and V _{DD}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.2\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.



(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \le V_{\text{DD}} \le 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.4		39	μs
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.8		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	,	0		Vdd	V
		ANI16 to ANI19		0		VDD	V
		Internal reference voltage (HS (high-speed main) mode)			V _{BGR} Note 3		V
		Temperature sensor output (HS (high-speed main) mod	0	١	/TMPS25 Note	3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM} ^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	t CONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

3.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μs

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)



3.6.3 Programmable gain amplifier

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9Vdd/	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	s				±1.5	%
		32 times					±2	%
Slew rate ^{Note 1}	SRrpga	Rising edge	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	4, 8 times	4			V/µs
				16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.8			V/µs
				16, 32 times	0.5			V/µs
	SRFPGA	Falling	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	4, 8 times	3.2			V/µs
		edge		16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.2			V/µs
				16, 32 times	0.5			V/µs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 tim	4, 8 times		5			μs
		16, 32 t	16, 32 times		10			μs

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Notes 1. When $V_{IPGA} = 0.1V_{DD}/gain$ to $0.9V_{DD}/gain$.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

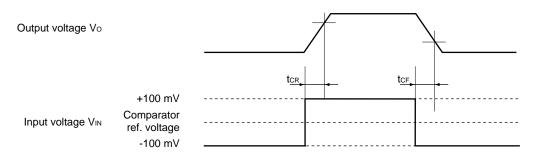
Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.



3.6.4 Comparator

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		Vdd	V
		СМРСОМ	0.045		0.9Vdd	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3~V \leq V_{\text{DD}} \leq 5.5~V$	1			μs
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	3			μS
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μs

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.
- **Remark** These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.



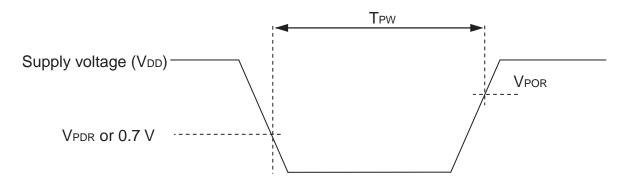


3.6.5 POR circuit characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.62	V
	VPDR	Power supply fall time	1.44	1.50	1.61	V
Minimum pulse width ^{Note}	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode (TA = -40 to +125°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.97	4.06	4.25	V
voltage	roltage		Power supply fall time	3.89	3.98	4.15	V
	VLVD1	Power supply rise time	3.67	3.75	3.93	V	
			Power supply fall time	3.59	3.67	3.83	V
		VLVD2	Power supply rise time	3.06	3.13	3.28	V
			Power supply fall time	2.99	3.06	3.20	V
		VLVD3	Power supply rise time	2.95	3.02	3.17	V
			Power supply fall time	2.89	2.96	3.09	V
		VLVD4	Power supply rise time	2.85	2.92	3.07	V
			Power supply fall time	2.79	2.86	2.99	V
		VLVD5	Power supply rise time	2.75	2.81	2.95	V
			Power supply fall time	2.70	2.75	2.88	V
Minimum pı	ulse width	t∟w		300			μs
Detection d	elay time					300	μs



LVD Detection Voltage of Interrupt & Reset Mode ($T_A = -40$ to +125°C, $V_{PDR} \le V_{DD} \le 5.5$ V, $V_{SS} = 0$ V)

Parameter	Symbol	Con	Conditions			MAX.	Unit
Interrupt and reset	Interrupt and reset VLVD0 VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage: 2.7				2.75	2.88	V
mode	VLVD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	3.07	V
			Falling interrupt voltage	2.79	2.86	2.99	V
	VLVD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
			Falling interrupt voltage	2.89	2.96	3.09	V
	VLVD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.25	V
			Falling interrupt voltage	3.89	3.98	4.15	V

3.6.7 Supply voltage rise inclination characteristics

(T_A = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

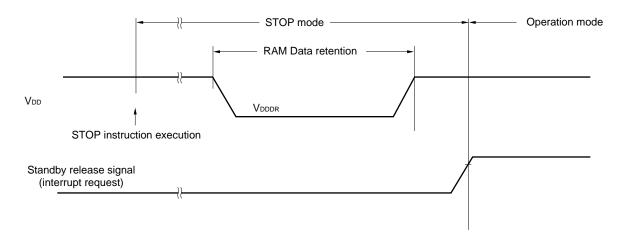
Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 33.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

(T_A = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage ^{Note 2}	VDDDR		1.47 ^{Note 1}		5.5	V

- **Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.





3.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fськ	$2.7~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, $T_A = 85^{\circ}C^{Note 3, 4}$	1,000			Times
Number of data flash		Retained for 1 year, $T_A = 25^{\circ}C^{Note 3, 4}$		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, $T_A = 85^{\circ}C^{Note 3, 4}$	100,000			
		Retained for 20 years, $T_A = 85^{\circ}C^{Note 3, 4}$	10,000			

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 - 4. These are the average temperature of during the retainment.

3.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

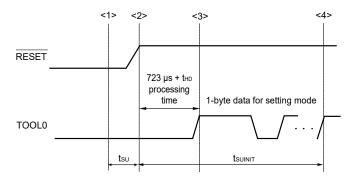
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps



3.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	ts∪	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



<R>

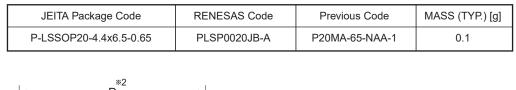
- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

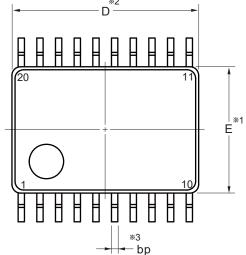


4. PACKAGE DRAWINGS

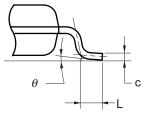
<R> 4.1 20-pin Products

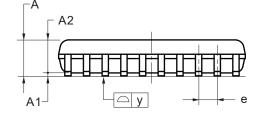
R5F1076CGSP#V0, R5F1076CGSP#X0, R5F1076CMSP#V0, R5F1076CMSP#X0





detail of lead end





NOTE

1.Dimensions "%1" and "%2" do not include mold flash.

2.Dimension "X3" does not include trim offset.



	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
Е	4.40±0.10
HE	6.40±0.20
А	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 + 0.10 - 0.05
С	0.15 + 0.05 - 0.02
L	0.50±0.20
У	0.10
θ	0° to 10°

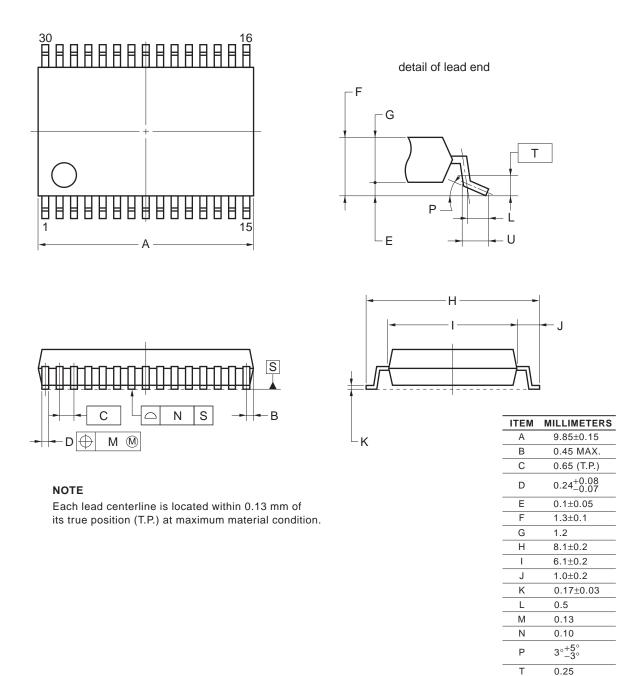
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4.2 30-pin Products

R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0, R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



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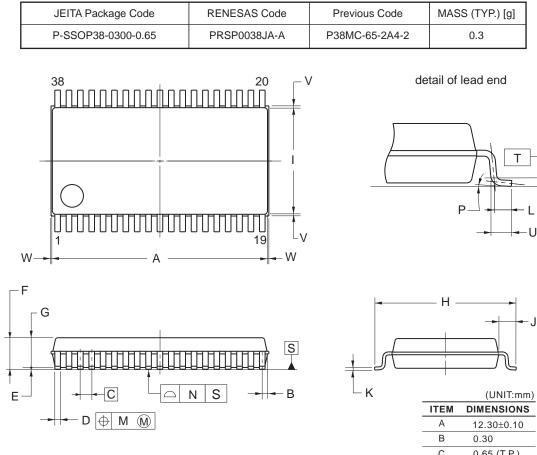
U

0.6±0.15



4.3 38-pin Products

R5F107DEGSP#V0, R5F107DEGSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0



NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

А	12.30±0.10
В	0.30
С	0.65 (T.P.)
D	$0.32\substack{+0.08\\-0.07}$
E	0.125±0.075
F	2.00 MAX.
G	1.70±0.10
Н	8.10±0.20
I	6.10±0.10
J	1.00±0.20
К	$0.17\substack{+0.08 \\ -0.07}$
L	0.50
М	0.10
Ν	0.10
Р	3° ^{+7°} 3°
Т	0.25(T.P.)
U	0.60±0.15
V	0.25 MAX.
W	0.15 MAX.

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Revision History

RL78/I1A Datasheet

			Description		
Rev.	Date	Page	Summary		
3.20	Sep 29, 2017	p.1	Modification of description in 1.1 Features		
		p.59	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes		
		p.102	Modification of figure in 3.10 Timing of Entry to Flash Memory Programming Modes		
		p.103	Modification of figure in 4.1 20-pin Products		

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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